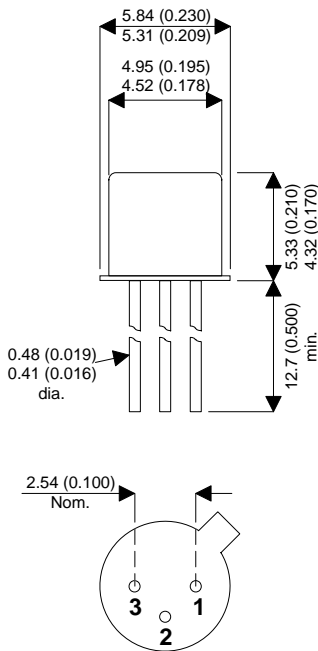


**MECHANICAL DATA**

Dimensions in mm (inches)



**TO-18 METAL PACKAGE**

**Underside View**

PIN 1 – Source    PIN 2 – Drain    PIN 3 – Gate  
 (Gate is connected to case)

**JFET SWITCHING  
 N CHANNEL- DEPLETION**

**FEATURES**

- LOW ON RESISTANCE
- FAST SWITCHING
- MILITARY OPTIONS AVAILABLE

**APPLICATIONS:**

- SWITCHING APPLICATIONS

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$V_{DS}$	Drain–Source Voltage	40V
$V_{DG}$	Drain–Gate Voltage	40V
$V_{GS}$	Gate–Source Voltage	40V
$I_{GF}$	Forward Gate Current	50mA
$P_D$	Total Device Dissipation @ $T_C = 25^{\circ}C$	1.8W
	Derate above $25^{\circ}C$	10mW/ $^{\circ}C$
$T_J$	Operating Junction Temperature Range	-65 to +175 $^{\circ}C$
$T_{STG}$	Storage Temperature Range	-65 to +175 $^{\circ}C$

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>OFF CHARACTERISTICS</b>					
$V_{(BR)GSS}$	Gate Source Breakdown Voltage <sup>1</sup>	$I_G = 1.0\mu\text{A}$ $V_{DS} = 0$	40		V
$I_{GSS}$	Gate Reverse Current	$V_{GS} = 20\text{V}$ $V_{DS} = 0$		0.1	nA
		$V_{GS} = 20\text{V}$ $V_{DS} = 0$ $T_A = 150^\circ\text{C}$		0.2	$\mu\text{A}$
$V_{GS}$	Gate Source Voltage	$V_{DS} = 20\text{V}$ $I_D = 1.0\text{nA}$	-0.2	-5	V
$V_{GS(f)}$	Gate Source Forward Voltage	$I_G = 1.0\text{mA}$ $V_{DS} = 0$		1.0	V
$I_{D(off)}$	Drain Cut-off Current	$V_{GS} = 7\text{V}$ $V_{DS} = 20\text{V}$		0.1	nA
		$V_{GS} = 7\text{V}$ $V_{DS} = 20\text{V}$ $T_A = 150^\circ\text{C}$		0.2	$\mu\text{A}$
<b>ON CHARACTERISTICS</b>					
$I_{DSS}$	Zero Gate voltage Drain Current <sup>1</sup>	$V_{GS} = 0\text{V}$ $V_{DS} = 20\text{V}$	25	75	mA
$V_{DS(on)}$	Drain Source On-Voltage	$I_D = 6\text{mA}$ $V_{GS} = 0$		0.4	V
$r_{DS(on)}$	Static Drain Source On Resistance	$I_D = 1.0\text{mA}$ $V_{GS} = 0$		60	$\Omega$
<b>ELECTRICAL CHARACTERISTICS</b>					
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}$ $V_{DS} = 20\text{V}$ $f = 1.0\text{MHz}$		14	pF
$C_{rss}$	Reverse Transfer Capacitance	$V_{GS} = 7\text{V}$ $V_{DS} = 0\text{V}$ $f = 1.0\text{MHz}$		3.5	
<b>SMALL SIGNAL CHARACTERISTICS</b>					
$r_{ds(on)}$	Drain-Source "ON" Resistance	$V_{GS} = 0\text{V}$ $I_D = 0$ $f = 1.0\text{kHz}$		60	$\Omega$
<b>SWITCHING CHARACTERISTICS</b>					
$t_{on}$	Turn-On Time	$I_{D(on)} = 6\text{mA}$		15	ns
$t_{off}$	Turn-Off Time	$V_{GS(on)} = 7\text{V}$		35	
$t_r$	RiseTime	$I_{D(on)} = 6\text{mA}$		5.0	
$t_f$	FallTime	$V_{GS(off)} = 7\text{V}$		20	

- 1) Pulse test : Pulse Width < 100 $\mu\text{s}$  ,Duty Cycle < 2%
- 2)  $f_t$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.